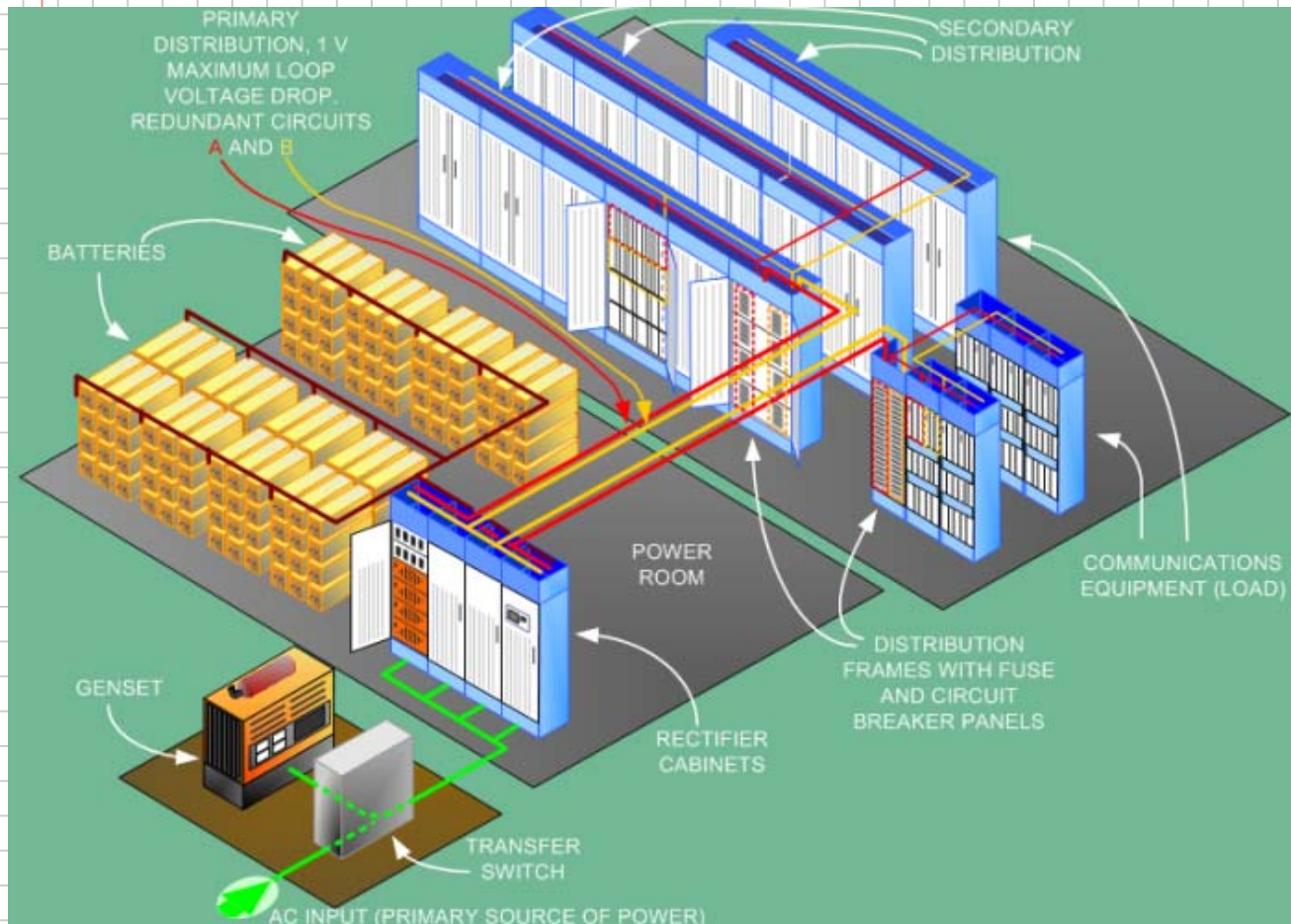
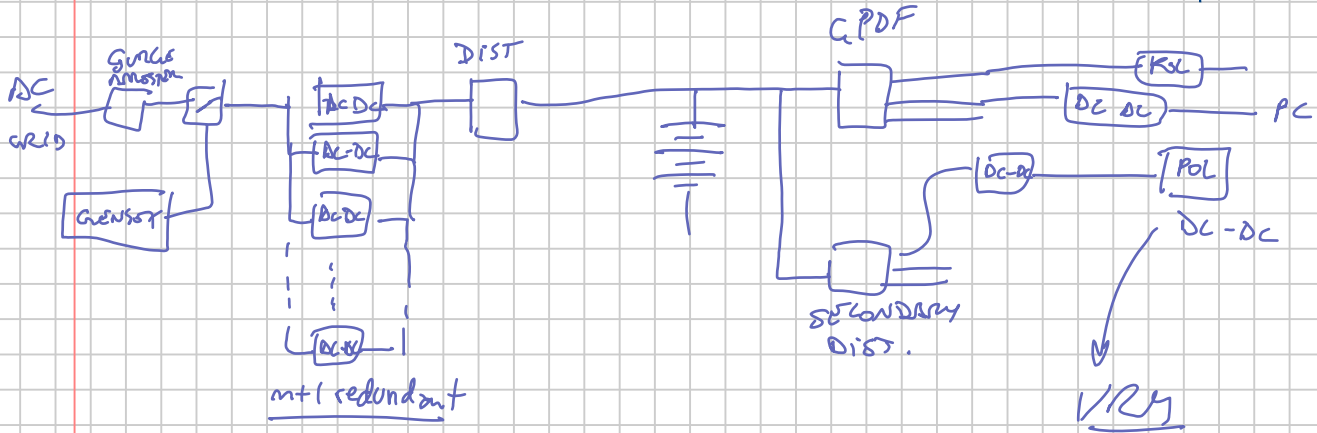


# Real components

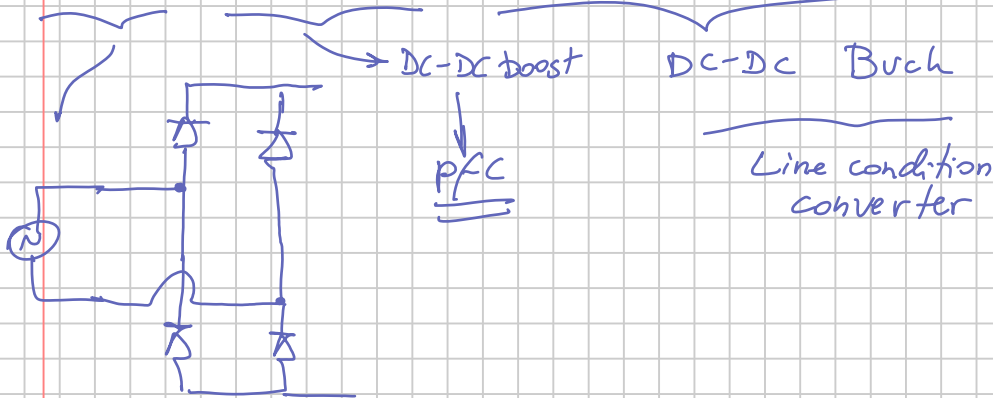
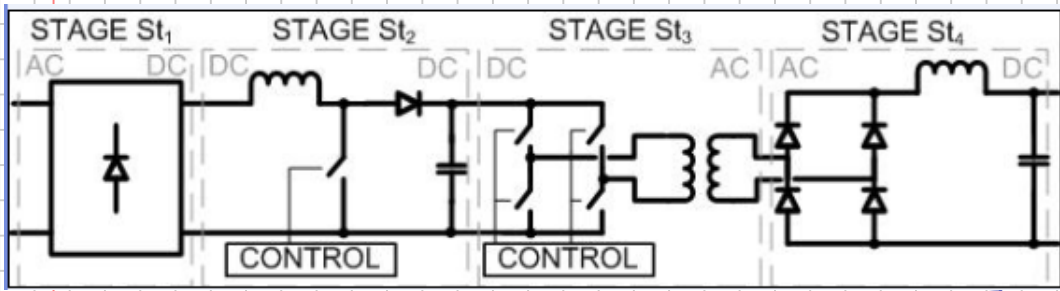
## Real components

Consider a telecom power systems



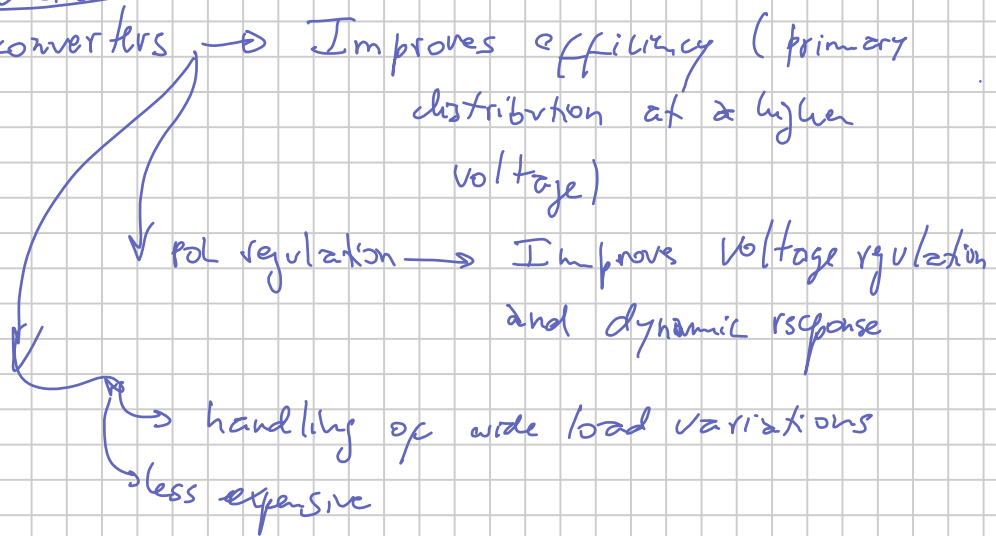
( See ppt )

# Rectifier

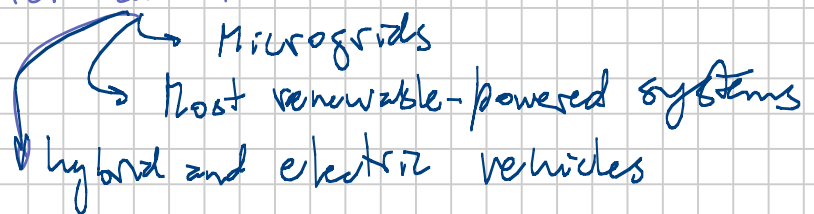


## Distributed architecture

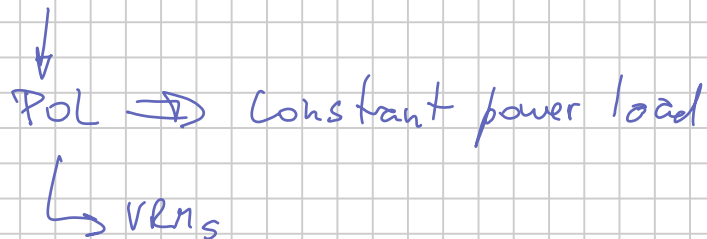
Cascade of converters



## Other systems with similar architectures

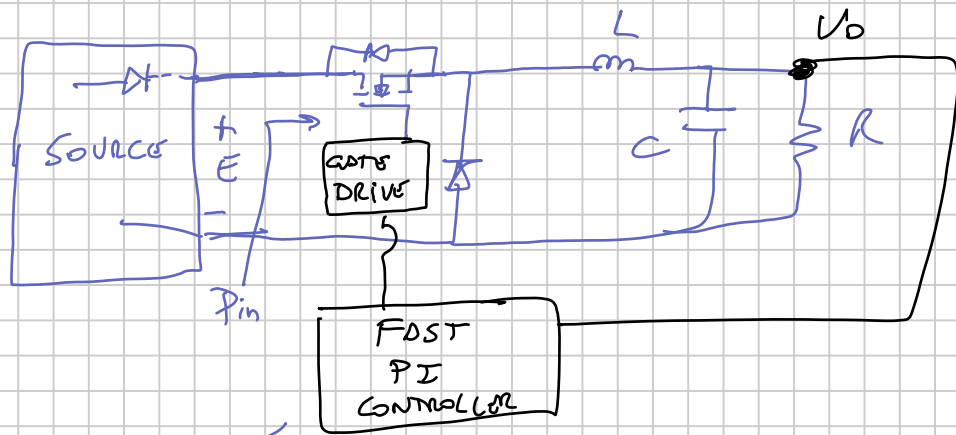


Real components → loads



Let's see first constant power loads

Assume a dc-dc buck converter acting as a POL converter



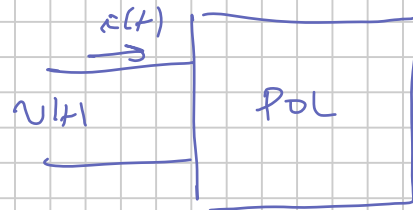
Since the controller is fast,  $V_o \approx \text{constant}$  → regardless of changes in the input  
 If  $V_o$  is constant,  $\frac{V_o^2}{R} = P_{out}$  is constant

Assuming there is no losses in the buck converter

$$P_{in} = P_{out}$$

$$P_{in} = \text{constant}$$

Real POL converters:



$$\left. \begin{aligned} i(t) &= 0 & \text{for } v(t) \leq V_{th} \\ i(t) &= \frac{P_L}{v(t)} & \text{for } v(t) > V_{th} \end{aligned} \right\}$$

Small signal behavior

$$g_i(t) = \left. \frac{\partial i}{\partial v} \right|_{V_o} \delta v(t) = - \frac{P_L}{V_o^2} \delta v(t)$$

$$\frac{\delta V(t)}{\delta i(t)} = \delta Z = -\frac{V_0^2}{P_2} < 0$$

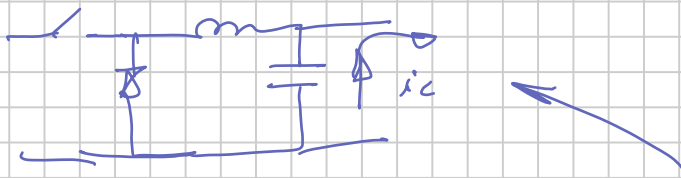
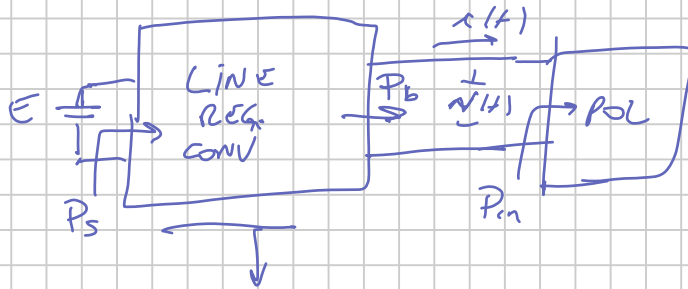
dynamic impedance

Assume that  $V$  drops  $\rightarrow \delta V(t) < 0$

$$\delta Z < 0$$

$\delta i(t) > 0 \rightarrow$  input current increases

destabilizing action



$$i_c = C \frac{dv_c}{dt} \rightarrow dv_c < 0 \text{ (discharging)}$$

As  $i_c$  increases the capacitor discharges, so  $v_c$  drops more  
 making  $i_c$  to increase and the effect is  
 reinforced  $\Rightarrow$  voltage collapse

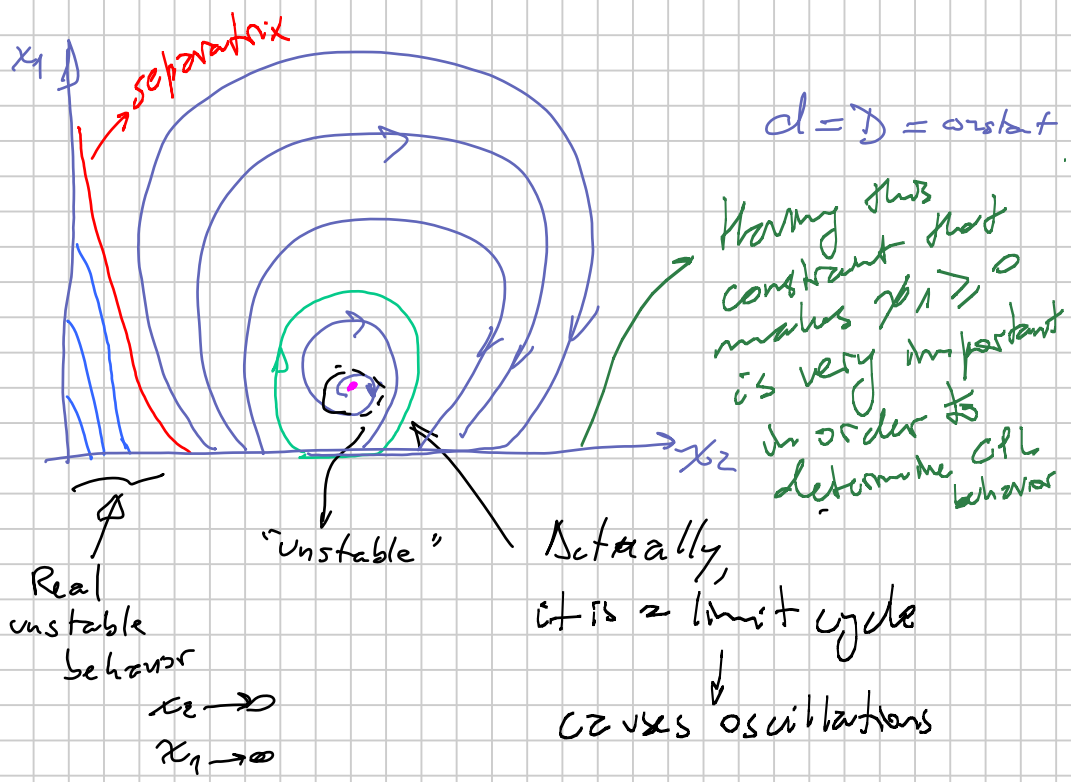
Global behavior

Assuming lossless converters

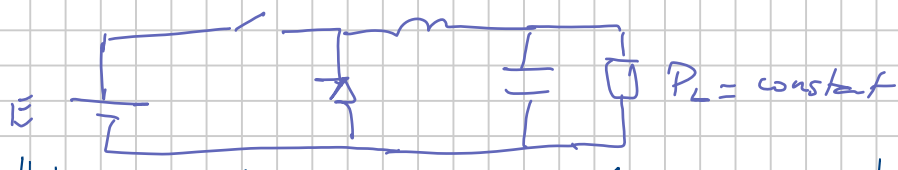
In reality, since  $P_s = P_b = P_{in} = P_L$  (steady state)  
 all extra power absorbed during transient cannot be  
 dissipated

$\Rightarrow$  Extra power  $\Rightarrow$  extra energy

remains oscillating between  
 the line reg. conv. L and C



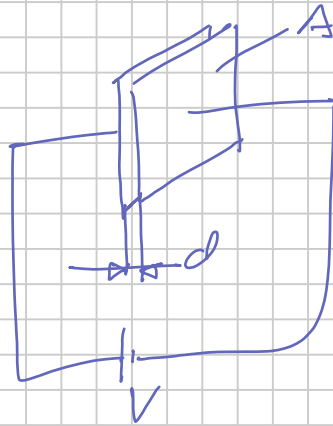
This is in the buck regulating converter but same effect happens with any dc-dc converter



We will be back here when we discuss controls

# Real capacitors

Ideal capacitor

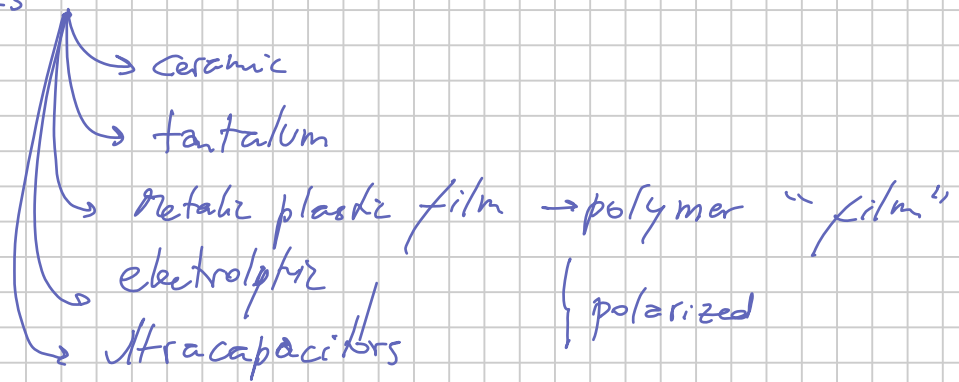


$$C = \frac{\epsilon A}{d} \rightarrow \text{only depends on material and geometry}$$

$$Q = CV \rightarrow i = C \frac{dv}{dt}$$

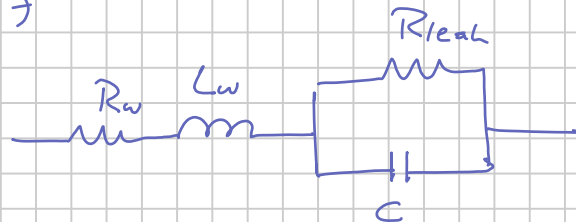
$$U = \frac{1}{2} CV^2$$

Capacitor types



From Leveh's book

Capacitor eq. model



$$Z(\omega) = R_w + j\omega L_w + \frac{1}{\frac{1}{R_{leak}} + j\omega C}$$

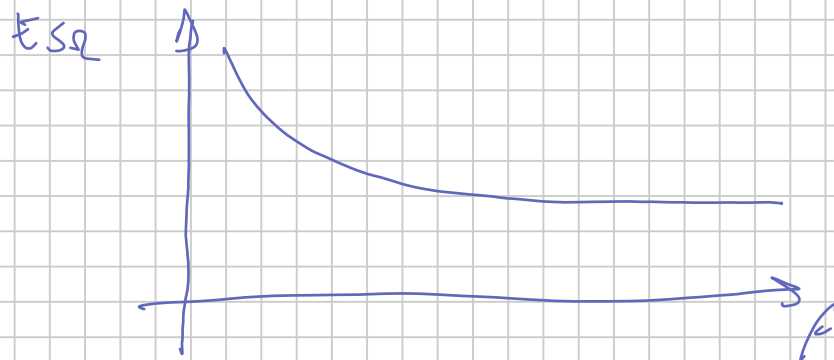
$$Z(\omega) = R_w + j\omega L_w + \frac{R_{leak}}{1 + j\omega C R_{leak}}$$

$$Z(\omega) = R_w + j\omega L_w + \frac{R_{leak} - j\omega C R_{leak}^2}{1 + \omega^2 C^2 R_{leak}^2}$$

↓  
Usually  $R_{leak} \rightarrow \infty$   
then  $\omega^2 C^2 R_{leak}^2 \gg 1$

$$Z(\omega) = R_w + \frac{1}{\omega^2 C^2 R_{leak}} + \frac{1}{j\omega C} + j\omega L_w$$

ESR( $\omega$ )  $\rightarrow$  Function of  $\omega$

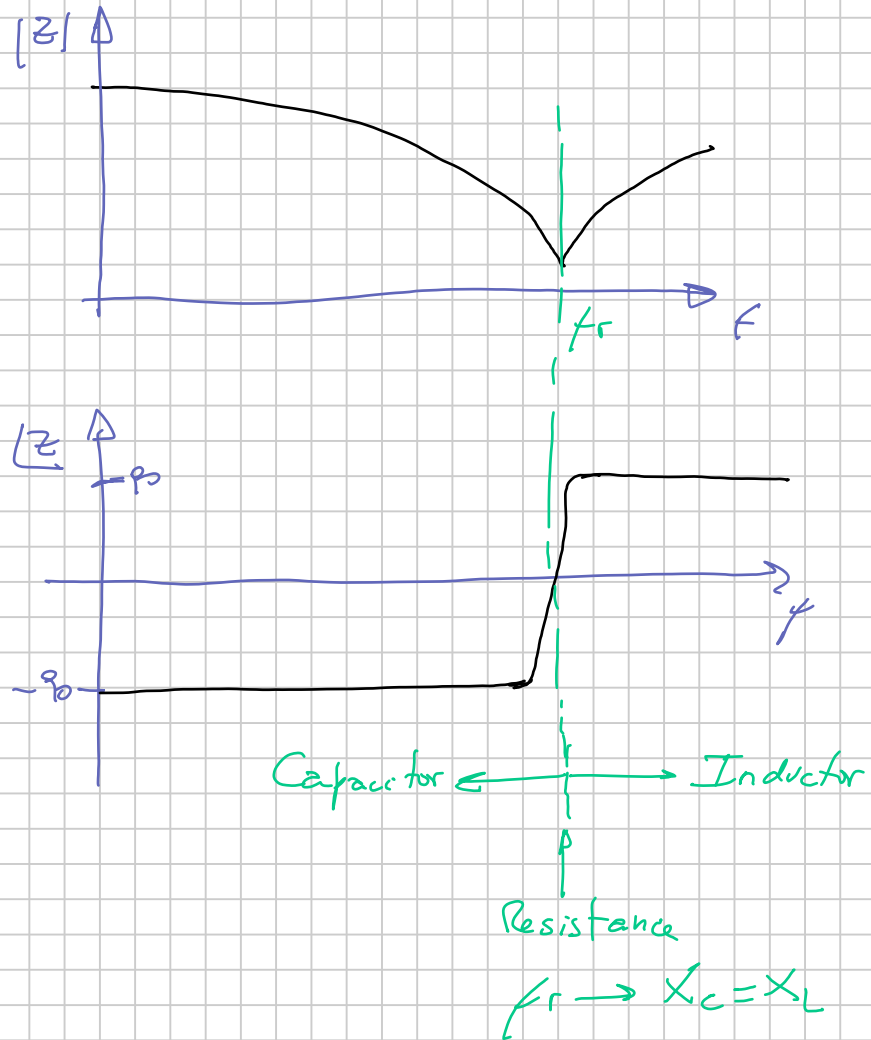


$$\tan \delta = \frac{ESR(\omega)}{X_c(\omega)} \approx \frac{1}{\omega R_{leak} C}$$

If  $R_{leak} = \frac{\rho d}{A}$

$$\tan \delta = \frac{1}{\omega \frac{\rho d}{A} C} = \frac{1}{\omega \rho \epsilon} \rightarrow \text{Independent of geometry}$$

## Frequency behavior



$f_r$  can be improved (made larger) by using // combination

Film  $\rightarrow$  high freq

mica  $\rightarrow$  " "

Ceramic  $\rightarrow$  " "

Electrolytic  $\rightarrow$  low freq, "high" ESR

Tantalum  $\rightarrow$  better than electrolytic

OS-CON  $\rightarrow$  A type of electrolytic

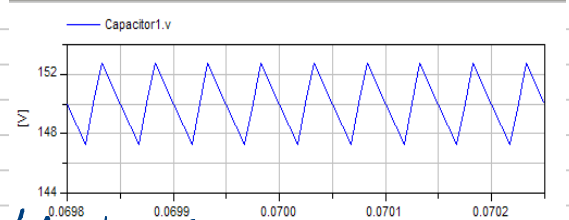
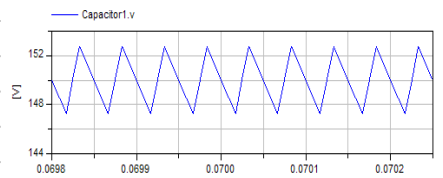
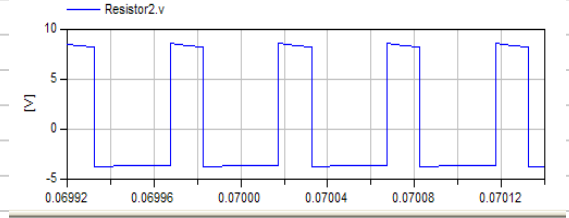
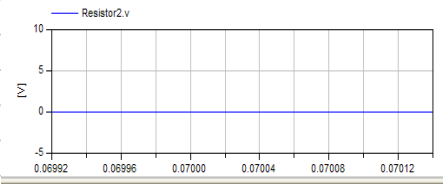
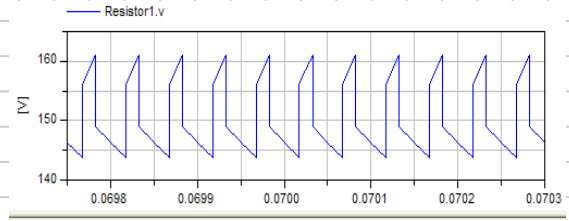
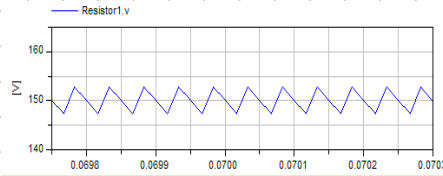
## Effect of ESR

obvious  $\rightarrow$  losses  $\rightarrow$  heat

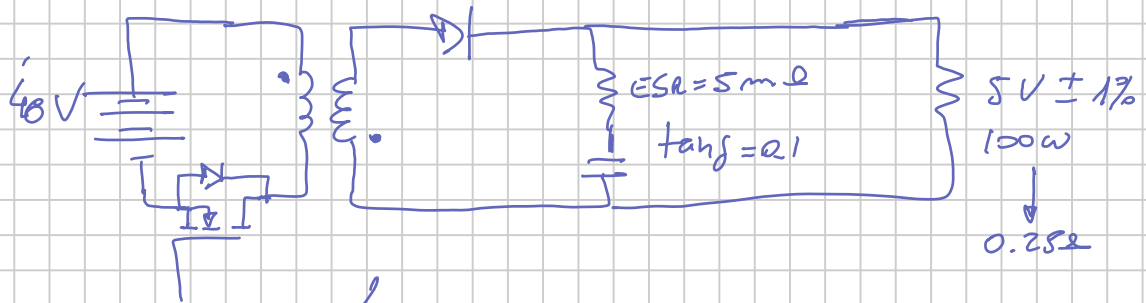
$\hookrightarrow$  A larger capacitor may be needed to provide a large



ESR jump

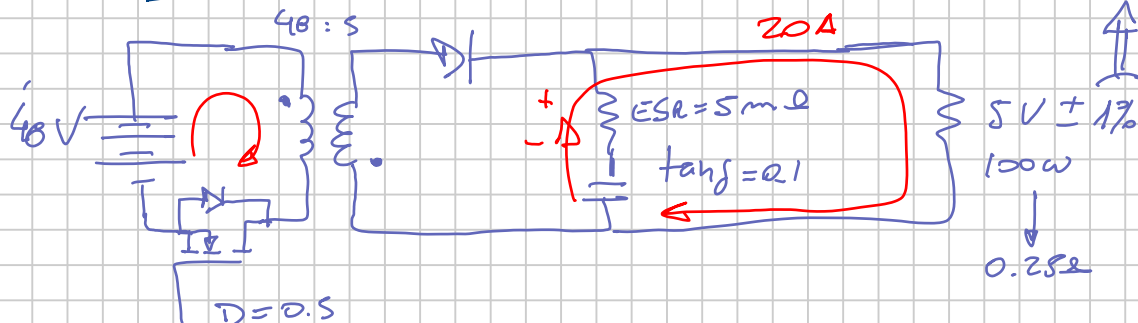


Let's see what happens with real capacitors in voltage regulation modules (VRMs)  
 ↳ A constant power load



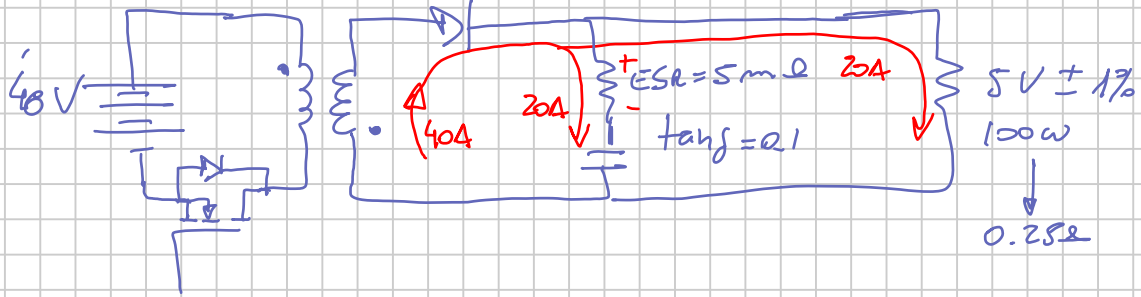
FLY Back

when switch is on



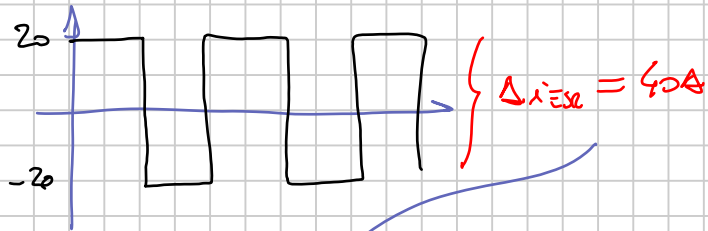
5V ± 1%  
 100W  
 ↓  
 0.25Ω  
 1V p-p  
 ↳ 0.05V<sub>p</sub>

when the switch is off



$$\Delta V_{load} = \Delta V_c + \Delta V_{ESR}$$

$$\Delta V_{ESR} = \Delta i_{ESR} \cdot ESR$$



$$\Delta V_{ESR} = 40 \cdot 0.05 = 0.2$$

Condition can not be met.

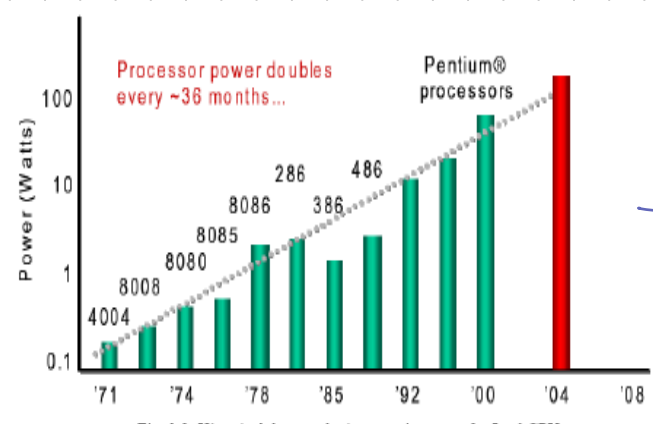
VRM → let's see voltage regulation modules and microprocessors as loads.

CPU → Faster clock speeds  
 → More transistors (CMOS)  
 → Moore's law → # transistors 2x every 2 years

$$P_{CPU} = A_v f C V_{dc}^2$$

(coming from  $Q = \frac{1}{2} C V_{dc}^2$ )  
 ↳ energy  
 ↳ "how many of all gates we are using"  
 ↳ capacitance of all gates  
 ↳ dc voltage  
 ↳ frequency  
 ↳ Activity factor

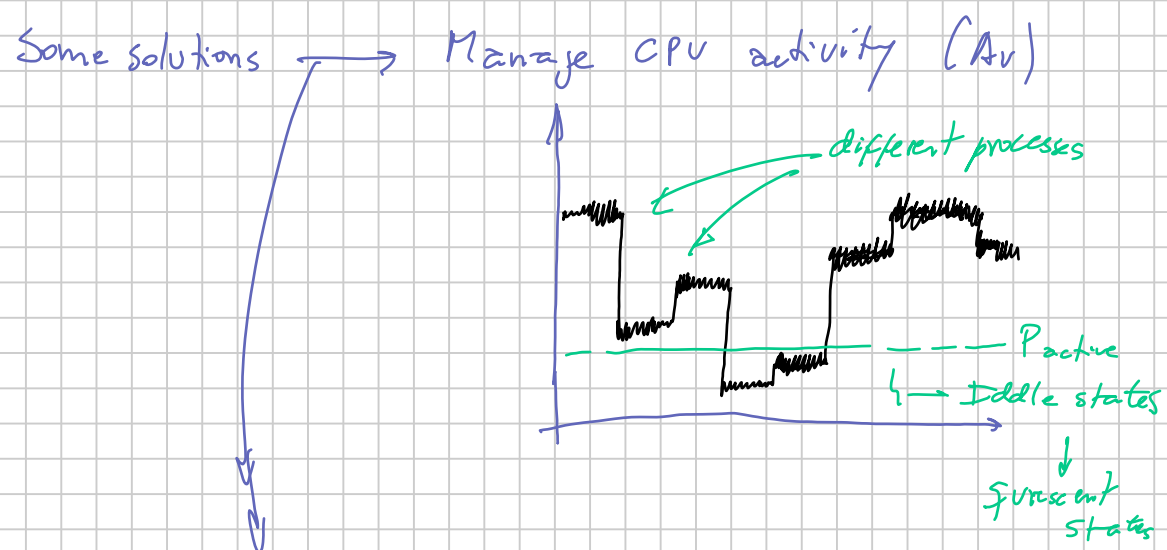
Power consumption issues → As size reduces, C increases  
 ↳ As the CPU speed increases, f increases



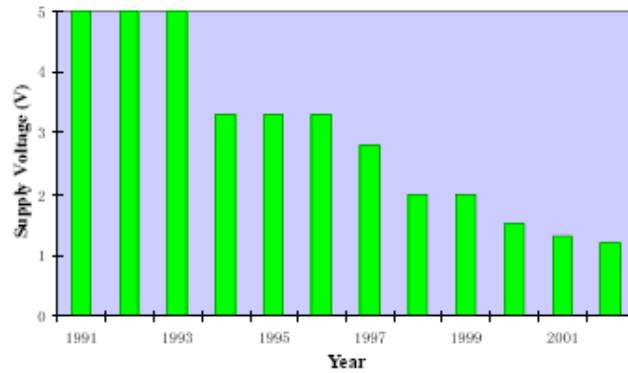
→ Power ⇒ Heat

Fig. 1.3. Historical data on the increase in power for Intel CPUs.

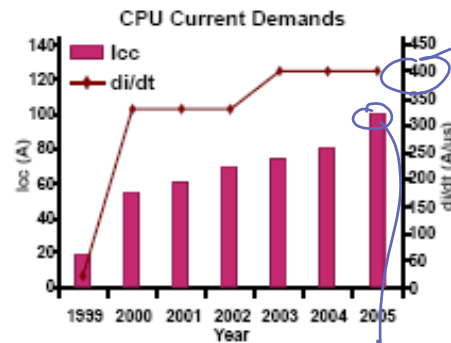
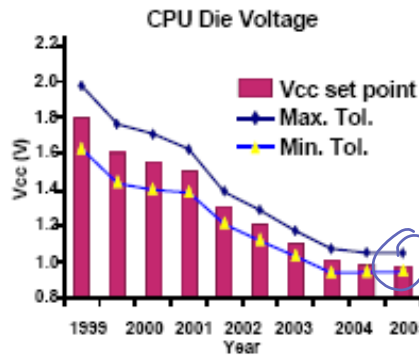
R. Mahajan, R Nair, V Wakharkar, J Swan, John Tang and G Vandentop, "Emerging Directions for Packing Technologies", Intel Technology Journal Vol.6 Issue 2, May 16, 2002.



Reduce voltage  $\rightarrow$  ( $P$  depends on  $V_{cc}^2$  so voltage reduction has big impact)



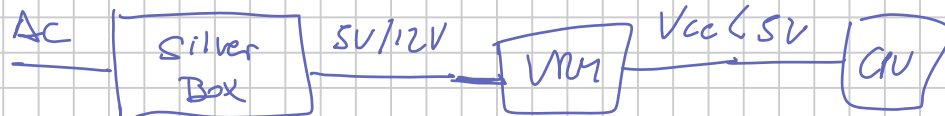
(Based on data from Intel Technology Symposium 2000, by Dr. Anthony J. Stratakos, Volterra)



1x faster tolerance @ 1V

> 100A

Typical architecture

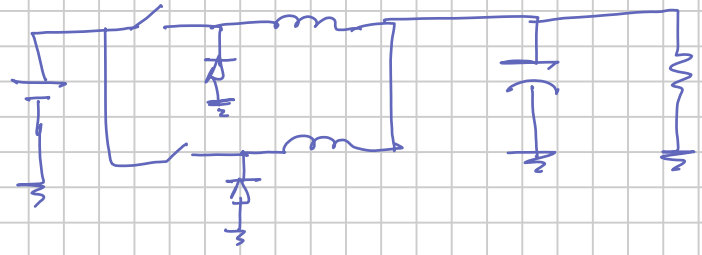


1st VRM topology  $\rightarrow$  buck

$\hookrightarrow$  As power increases  $\rightarrow$  high thermal demand on MOSFETS & inductors

$\rightarrow$  size (same power density)

Solutions → Use of multiphase buck



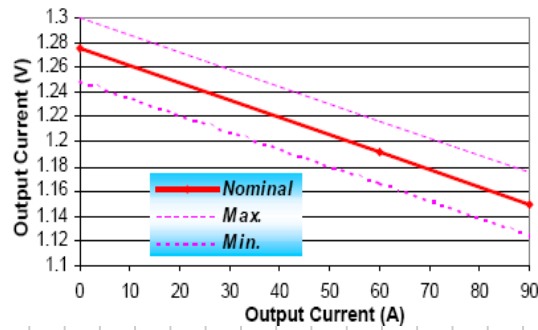
Increased voltage from 5V to 12V

Other problems → Fast load changes (slew rate)

↓ several kmps./μsec

↓ overshoots → shorter life

↓ undershoots → "blue screens"



↓ Power dissipation and distribution

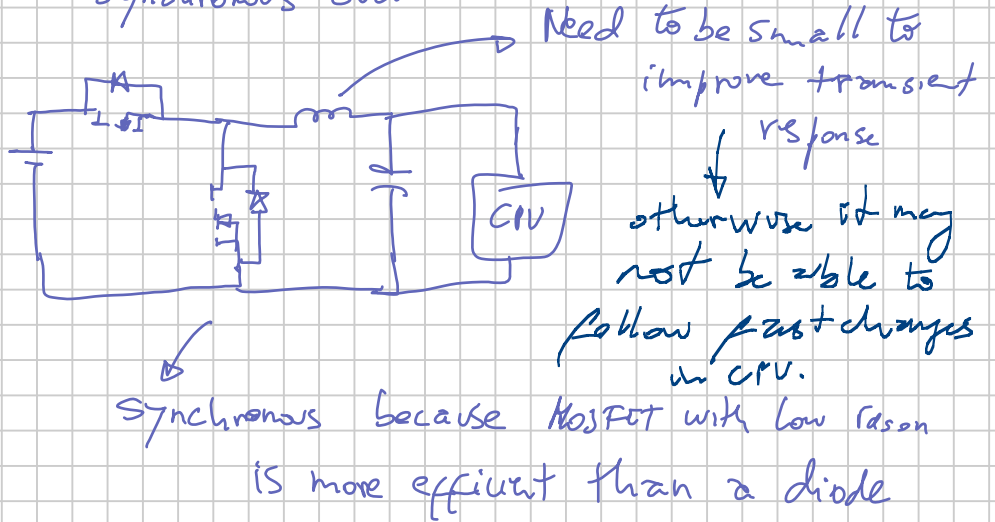
And of course → efficiency,

↓ OSCON caps → output caps → most expensive component  
↳ used to filter ripple and handling load

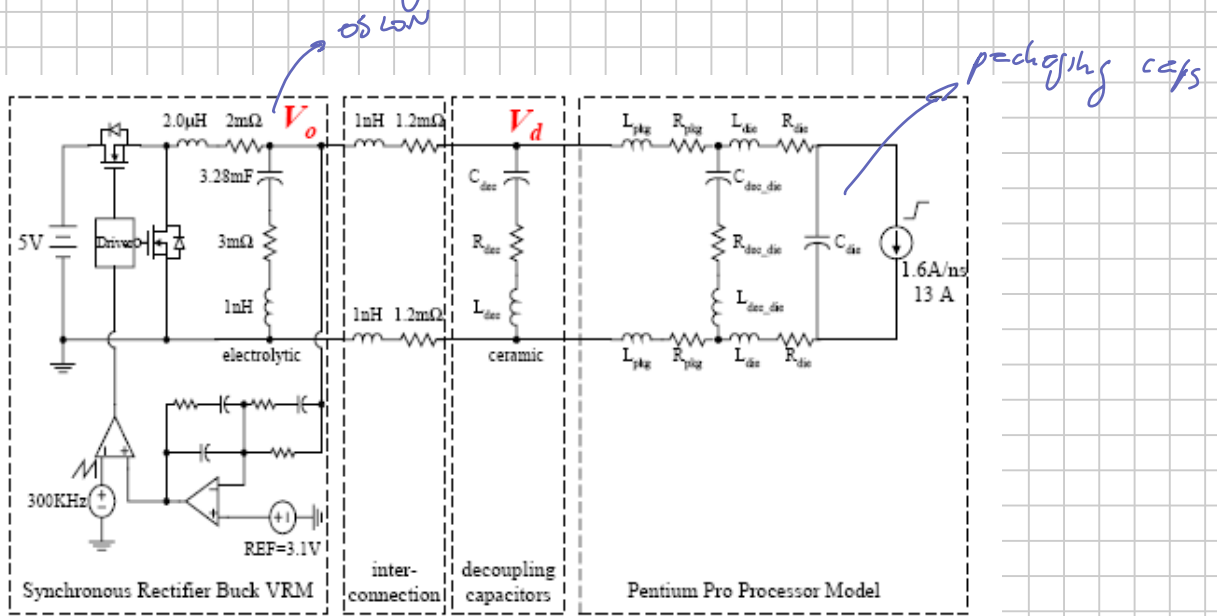
↓ Space → To minimize parasitic impedance VEM needs to be close to the CPU (takes CPU space)



Simplest var → Synchronous buck

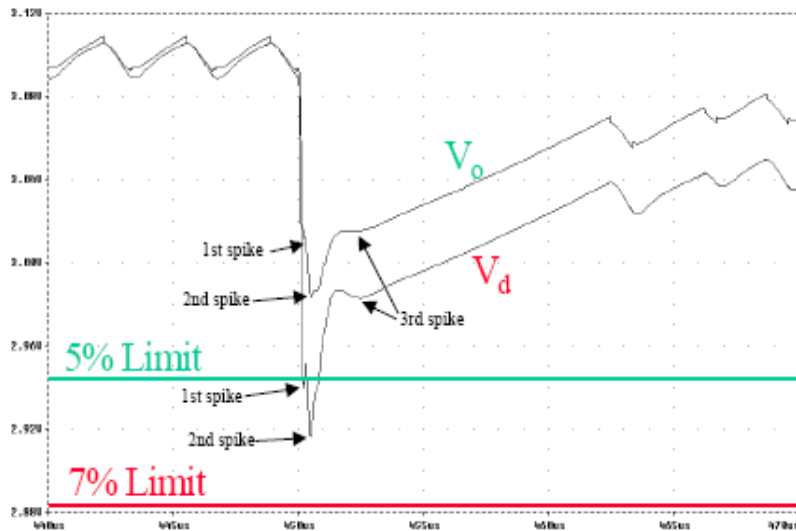


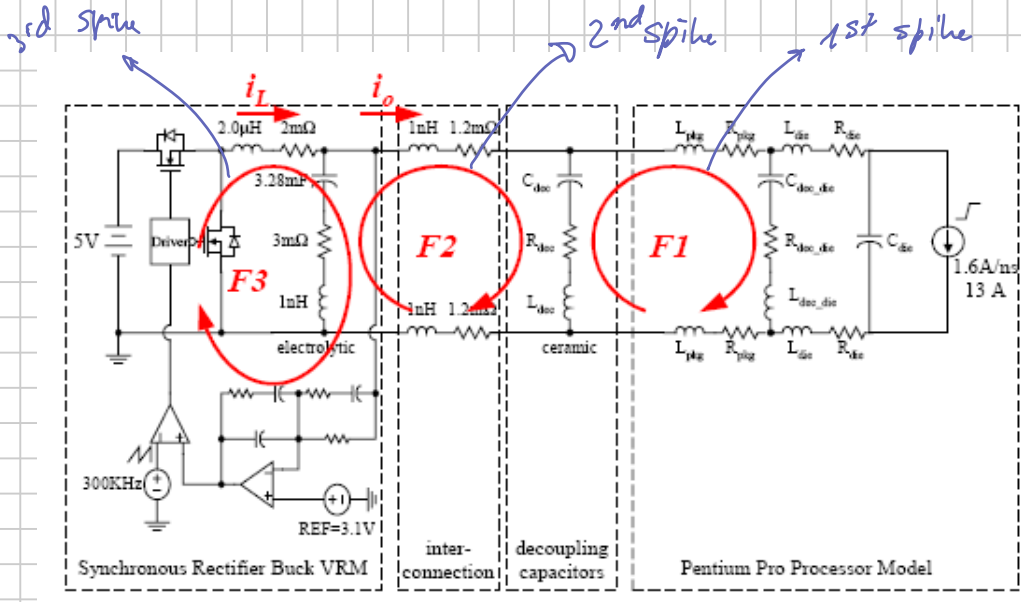
Multichannel interleaving improves transient issues



Transients:

Filter high frequency noise





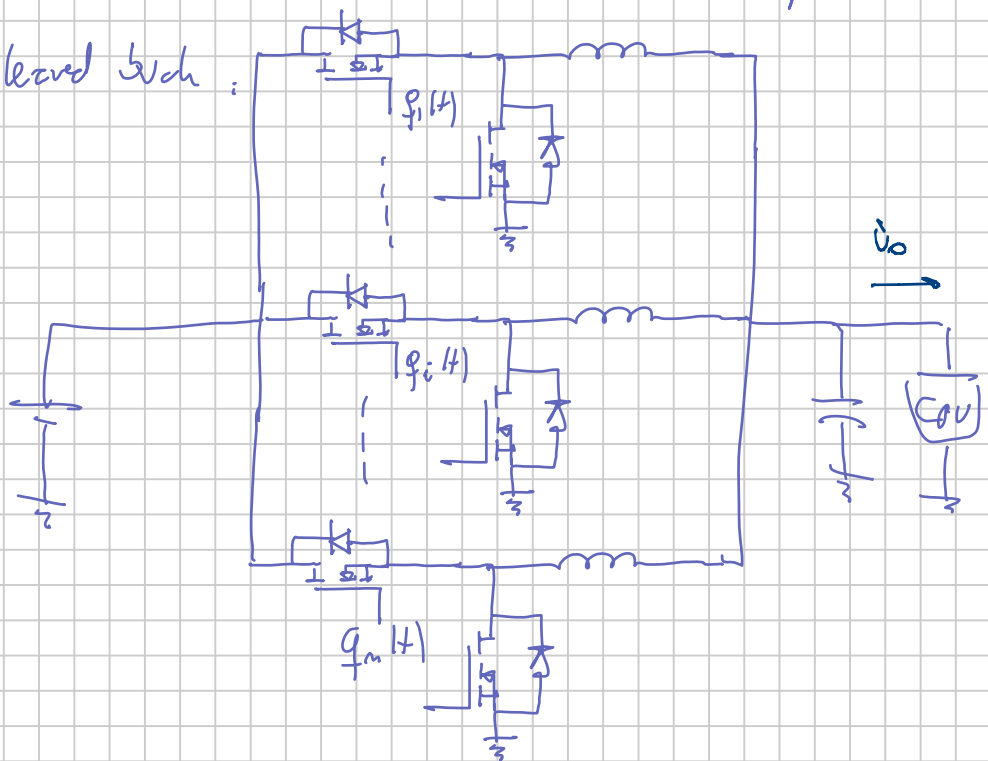
$$f_1 \gg f_2 \gg f_3$$

For smaller capacitance  $\rightarrow$  larger inductor slew rate  $\rightarrow$  smaller inductance

But  $\rightarrow$  smaller inductance  $\rightarrow$  larger inductor current ripple

larger output voltage ripple  
(more EMI, more losses in caps)

Solution: interleaved buck:

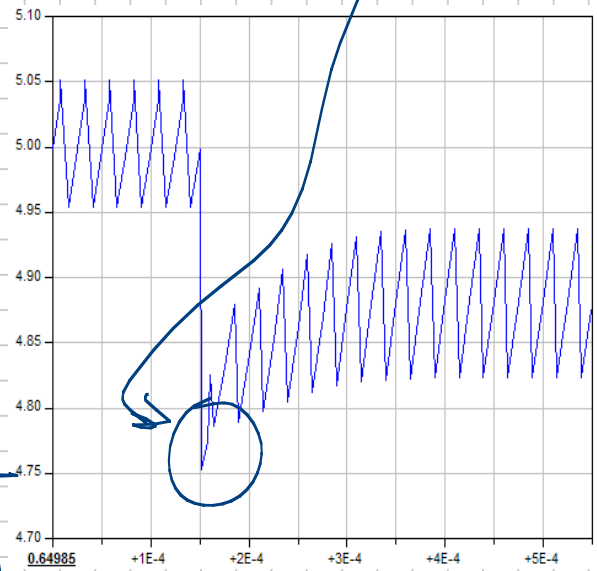
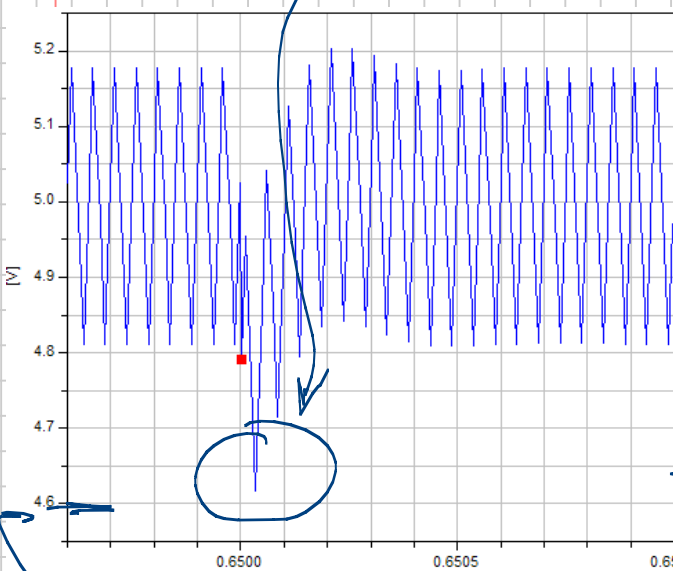
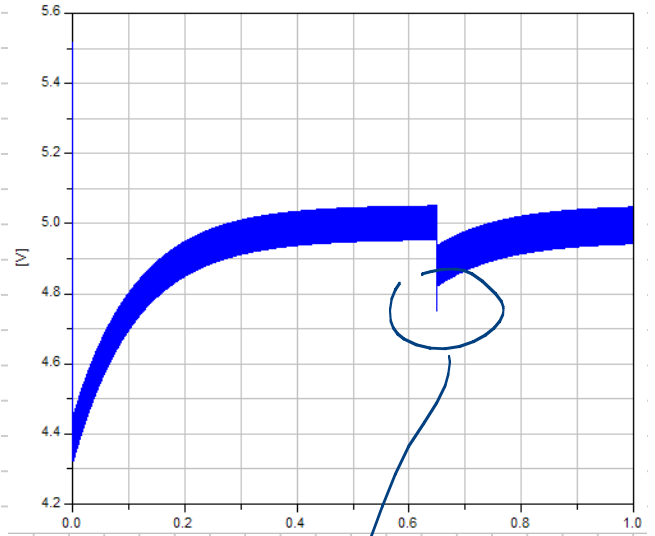
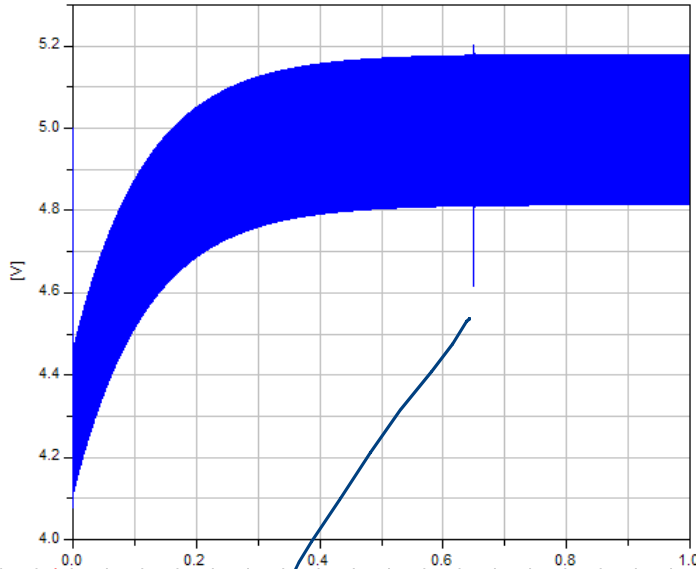


$$f_i(t) = f_1 \left( t + \frac{i 2\pi T}{m} \right)$$

$$E = 12V, C = 3mF, L = 10\mu H, R_c = 0.025, i_L = 10, 20A$$

$$k_i = 5, k_p = 0.5$$

$$\Delta I = 10A / \mu sec$$



Better than

Assume 2 phases:

$$\begin{cases} L\dot{x}_1 = f_{11}(t)E - x_2 \\ L\dot{x}_2 = f_{12}(t)E - x_2 \\ C\dot{x}_2 = x_1 + x_2 - i_o \end{cases}$$

$$\frac{di_o}{dt} = \dot{x}_1 + \dot{x}_2 - C\ddot{x}_2$$

$$\frac{1}{L} (f_{11}E - x_2) \quad \frac{1}{L} (f_{12}E - x_2)$$

$$\frac{di_o}{dt} = \frac{1}{L} (f_{11} + f_{12})E - \frac{2}{L} x_2 - C\ddot{x}_2$$

slow rate required by microprocessor



